

## PESDNC2FD12VBN

## **Bi-directional 12V Normal Capacitance ESD Protector**

#### Description

The PESDNC2FD12VBN protects sensitive semiconductor components from damage or upset due to electrostatic discharge (ESD) and other voltage induced transient events. They feature large cross-sectional area junctions for conducting high transient currents, offer desirable electrical characteristics for board level protection, such as fast response time, low operating voltage. It gives designer the flexibility to protect one bi-directional line in applications where arrays are not practical.

### Feature

- 90W peak pulse power per line (t<sub>P</sub> = 8/20µs)
- DFN1006-2L package
- Replacement for MLV(0402)
- Bidirectional configurations
- Response time is typically < 1ns</p>
- Low clamping voltage
- RoHS compliant
- Transient protection for data lines to IEC61000-4-2(ESD) ±30kV(air), ±30kV(contact);
  IEC61000-4-4 (EFT) 40A (5/50ns)

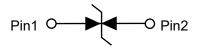
#### Applications

- Cellular phones
- Portable devices
- Digital cameras
- Power supplies

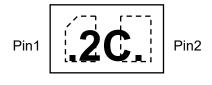
### **Mechanical Characteristics**

- Mounting position: Any
- Qualified max reflow temperature:260°C
- Device meets MSL 1 requirements
- DFN1006-2L without plating







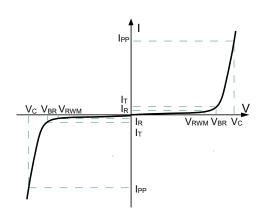


Marking (Top View)

### PESDNC2FD12VBN

## **Electronics Parameter**

Symbol	Parameter		
VRWM	Peak Reverse Working Voltage		
I <sub>R</sub>	Reverse Leakage Current @ V <sub>RWM</sub>		
VBR	Breakdown Voltage @ I⊤		
Iτ	Test Current		
IPP	Maximum Reverse Peak Pulse Current		
Vc	Clamping Voltage @ IPP		
P <sub>PP</sub>	Peak Pulse Power		
CJ	Junction Capacitance		
١F	Forward Current		
VF	Forward Voltage @ I <sub>F</sub>		



## Electrical characteristics per line@25 $^{\circ}$ C (unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Peak Reverse Working Voltage	VRWM				12	V
Breakdown Voltage	V <sub>BR</sub>	It = 1mA	14		17	V
Reverse Leakage Current	I <sub>R</sub>	V <sub>RWM</sub> = 12V Т=25℃			1.0	μA
Clamping Voltage <sup>(1)</sup>	Vc	TLP=16A tp=100ns		24		V
Dynamic resistance <sup>(1)</sup>	R <sub>DYN</sub>			0.45		Ω
Clamping Voltage <sup>(2)</sup>	Vc	I <sub>PP</sub> =1A t <sub>P</sub> = 8/20µs		16	18	V
Clamping Voltage <sup>(2)</sup>	Vc	I <sub>PP</sub> =4A t <sub>P</sub> = 8/20µs		21	23	V
Junction Capacitance	CJ	V <sub>R</sub> =0V f = 1MHz		13	20	pF

Notes: 1. TLP parameter: Z0=50Ω, tp=100ns, tr=2ns, averaging window from 60ns to 80ns. R<sub>DYN</sub> is calculated from 4A to 16A.

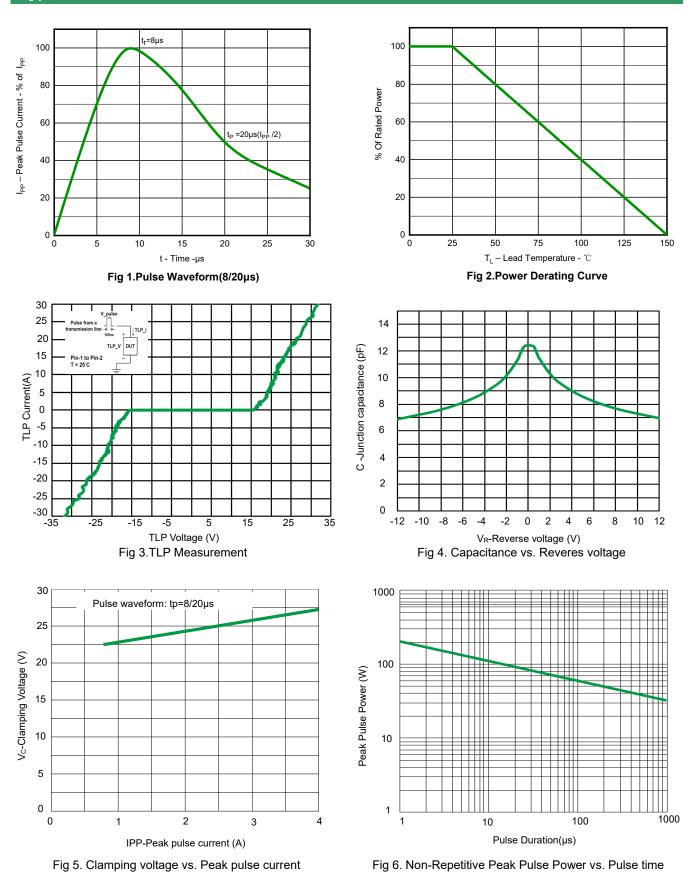
2. Non-repetitive current pulse, according to IEC61000-4-5.

## Absolute maximum rating@25°C

Rating	Symbol	Value	Unit
Peak Pulse Power (t <sub>p</sub> =8/20µs)	P <sub>pp</sub>	90	W
Peak Pulse Current (t <sub>p</sub> =8/20µs)	I <sub>pp</sub>	4	А
Operating Temperature	TJ	-55 to 150	°C
Storage Temperature	Тѕтс	-55 to 150	°C

### PESDNC2FD12VBN

## **Typical Characteristics**



#### PESDNC2FD12VBN

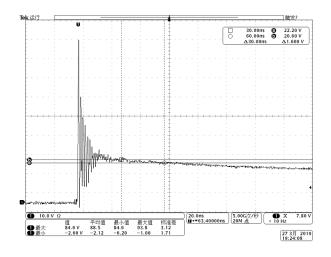


Fig 7. ESD clamping voltage (IEC61000-4-2 +8kV contact)

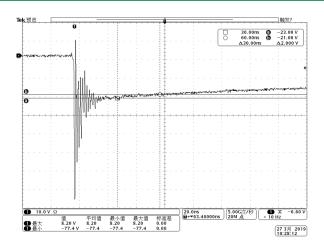
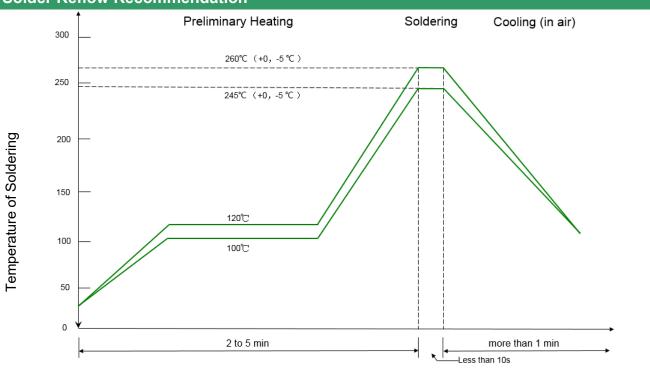


Fig 8. ESD clamping voltage (IEC61000-4-2-8kV contact)

#### Solder Reflow Recommendation



Remark: Pb free for 260°C; Pb for 245°C.

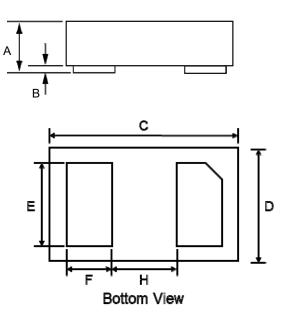
#### PCB Design

For TVS diodes a low-ohmic and low-inductive path to chassis earth is absolutely mandatory in order to achieve good ESD protection. Novices in the area of ESD protection should take following suggestions to heart:

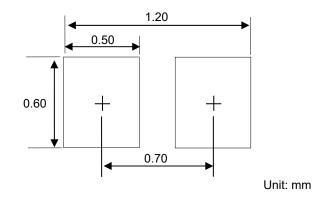
- > Do not use stubs, but place the cathode of the TVS diode directly on the signal trace.
- Do not make false economies and save copper for the ground connection.
- Place via holes to ground as close as possible to the anode of the TVS diode.
- Use as many via holes as possible for the ground connection.
- > Keep the length of via holes in mind! The longer the more inductance they will have.

## PESDNC2FD12VBN

# Product dimension (DFN1006-2L)



Dim	Millim	neters	Inches		
	MIN	MAX	MIN	МАХ	
А	0.40	0.55	0.016	0.022	
В	0.00	0.05	0.000	0.002	
С	0.90	1.10	0.035	0.043	
D	0.55	0.65	0.022	0.026	
E	0.35	0.55	0.014	0.022	
F	0.15	0.30	0.006	0.012	
н	0.40 Тур.		0.015 Тур.		

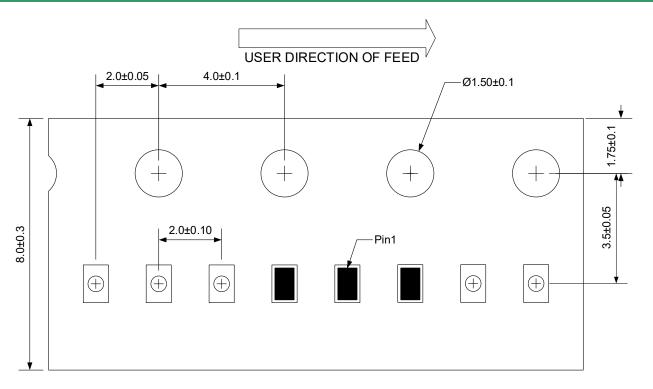


Suggested PCB Layout

# Ordering information

Device	Package	Reel	MPQ
PESDNC2FD12VBN	DFN1006-2L (Pb-Free)	7"	10000 / Tape & Reel

## Load with information



### Unit:mm

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